

IGBT MODULE (L series)

■ Features

- High Speed Switching
- Low Saturation Voltage
- Compact Package
- PCB Mounting Flexibility

■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply
- Industrial Machines, such as Welding Machines

■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings

Items		Symbols	Ratings	Units
Collector-Emitter Voltage		V _{CES}	600	V
Gate-Emitter Voltage		V _{GES}	±20	V
Collector Current	Continuous	I _C	15	A
	1ms	I _C pulse	30	
	Duty = 77%	-I _C	15	
	1ms	-I _C pulse	30	
Max. Power Dissipation		P _C	50	W
Operating Temperature		T _J	+150	°C
Storage Temperature		T _{stg}	-40 to +125	°C
Isolation Voltage	AC, 1min.	V _{is}	2000	V
Screw Torque		Mounting *1	17	kg·cm

*1 Recommendable Value 13 to 17kg·cm (M4)

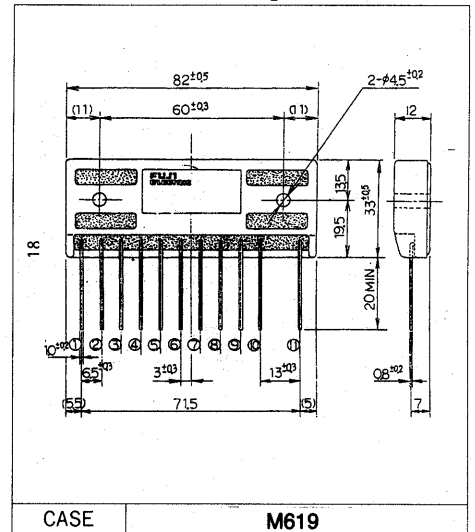
● Electrical Characteristics (T_J=25°C)

Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Zero Gate Voltage Collector Current	I _{CES}	V _{GE} =0V V _{CE} =600V T _J =25°C			1.0	mA
Gate-Emitter Leakage Current	I _{GES}	V _{CE} =0V V _{GE} =±20V			100	nA
Gate-Emitter Threshold Voltage	V _{GE(th)}	V _{CE} =20V I _C =15mA	3.0	4.5	6.0	V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	V _{GE} =15V I _C =15A		2.7	3.5	V
Input Capacitance	C _{ies}	V _{GE} =0V		1400		pF
Output Capacitance	C _{oes}	V _{CE} =10V		—		
Reverse Transfer Capacitance	C _{res}	f=1MHz		—		
Turn-on Time	t _{on}	V _{CC} =300V		0.4	0.8	μs
	t _r	I _C =15A		0.3	0.6	
Turn-off Time	t _{off}	V _{GE} =±15V		0.6	1.0	
	t _f	R _G =150Ω		0.2	0.35	
Diode Forward On-Voltage	V _F	I _F =15A V _{GE} =0V			2.5	V
Reverse Recovery Time	t _{rr}	I _F =15A -di/dt=50A/μs V _{GE} =-10V			300	ns

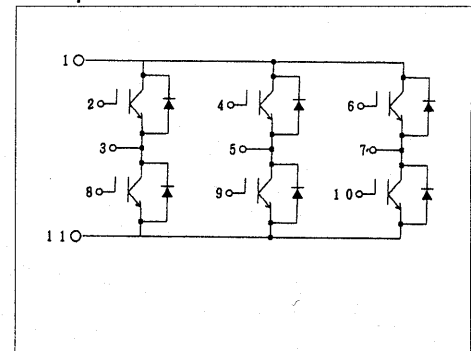
● Thermal Characteristics

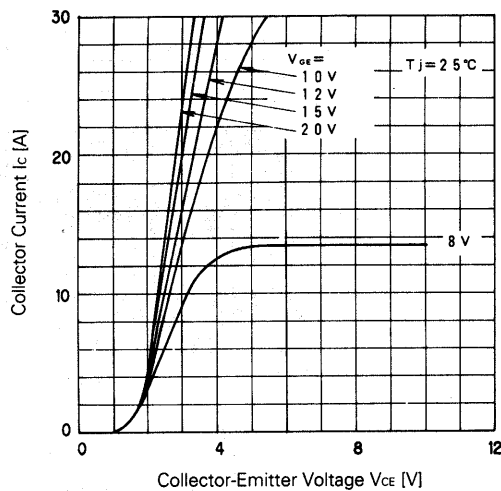
Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance	R _{th(j-c)}	IGBT			2.5	°C/W
	R _{th(j-c)}	Diode			4.30	
	R _{th(c-f)}	With Thermal compound		0.06		

■ Outline Drawings

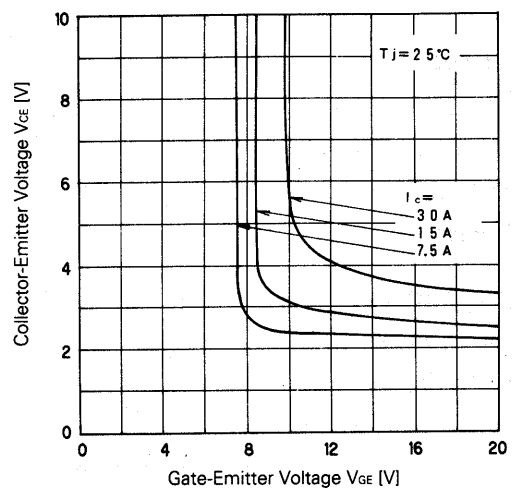


■ Equilavent Circuit Schematic

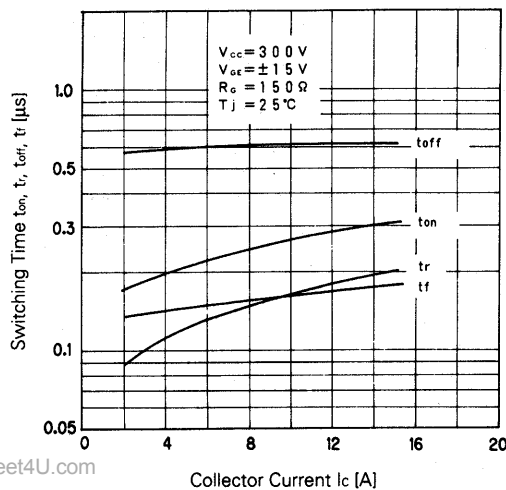




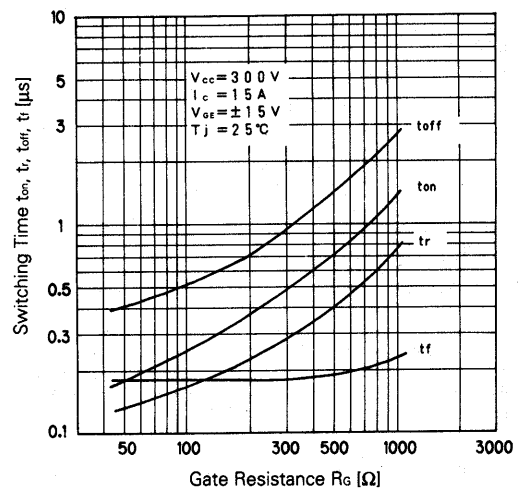
Collector Current vs. Collector-Emitter Voltage



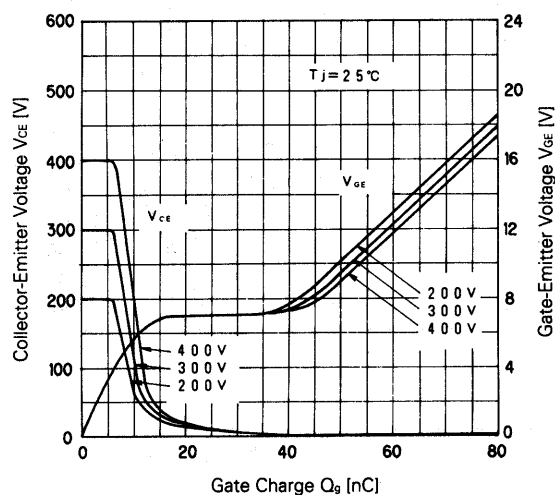
Collector-Emitter Voltage vs. Gate-Emitter Voltage



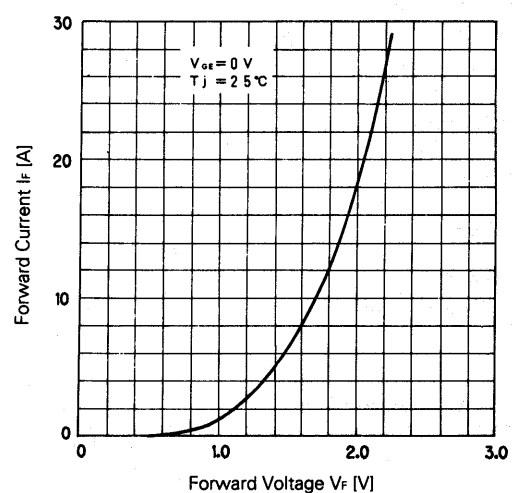
Switching Time



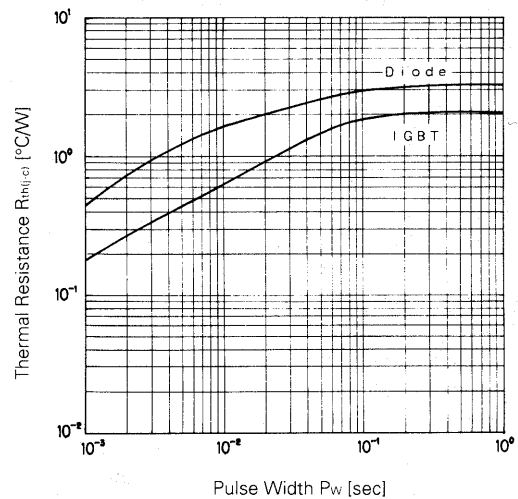
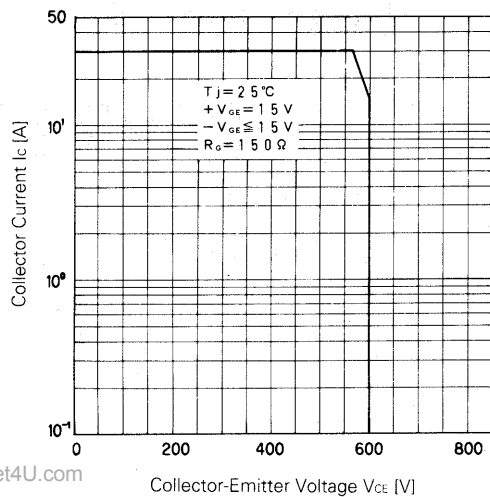
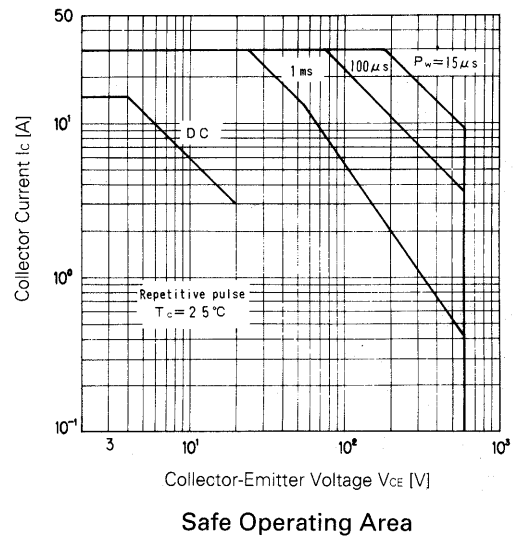
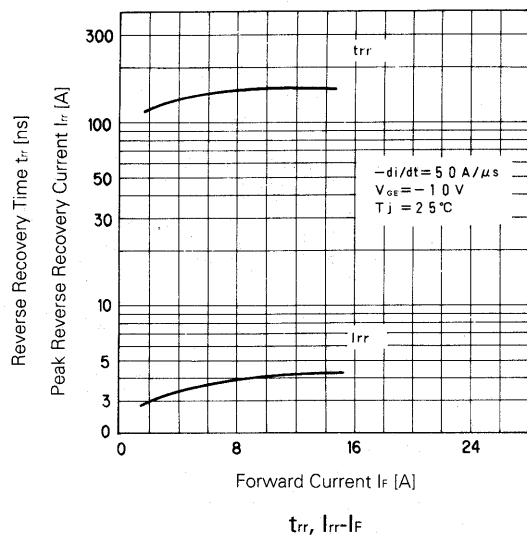
Switching Time-Gate Resistance



Dynamic Input Characteristic



Forward Voltage of Free Wheel Diode



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